



UNISONIC TECHNOLOGIES CO., LTD

UT3437

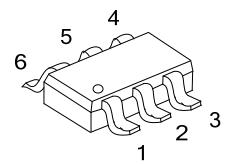
Power MOSFET

-1.4A, -150V P-CHANNEL (D-S)
POWER MOSFET

■ DESCRIPTION

The UTC **UT3437** is a P-channel MOSFET, it uses UTC's advanced technology to provide the customers with low gate charge, etc.

The UTC **UT3437** is suitable for active clamp circuits in DC/DC power supplies.



SOT-26

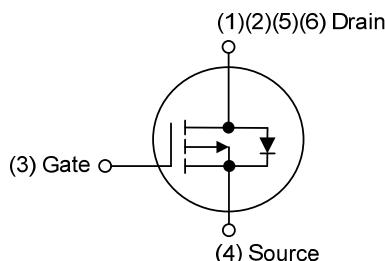
■ FEATURES

* $R_{DS(ON)} \leq 0.75 \Omega$ @ $V_{GS}=-10V$, $I_D=-1.4A$

$R_{DS(ON)} \leq 0.79 \Omega$ @ $V_{GS}=-6.0V$, $I_D=-1.0A$

* Low gate charge

■ SYMBOL



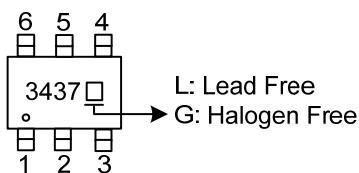
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment						Packing
Lead Free	Halogen Free		1	2	3	4	5	6	
UT3437L-AG6-R	UT3437G-AG6-R	SOT-26	D	D	G	S	D	D	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

UT3437G-AG6-R	(1)Packing Type (2)Package Type (3)Green Package	(1) R: Tape Reel (2) AG6: SOT-26 (3) G: Halogen Free and Lead Free, L: Lead Free
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■ MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	V_{DSS}	-150	V
Gate-Source Voltage	V_{GSS}	± 20	V
Continuous Drain Current ($T_C=25^\circ\text{C}$)	I_D	-1.4	A
Pulsed Drain Current	I_{DM}	-5	A
Peak Diode Recovery dv/dt (Note 3)	dv/dt	1.2	V/ns
Maximum Power Dissipation	P_D	1.1	W
Junction Temperature	T_J	-55 ~ 150	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-55 ~ 150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. $I_{SD} \leq -1.2\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$.

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	113	$^\circ\text{C/W}$

Note: Surface Mounted on 1" x 1" FR4 board.

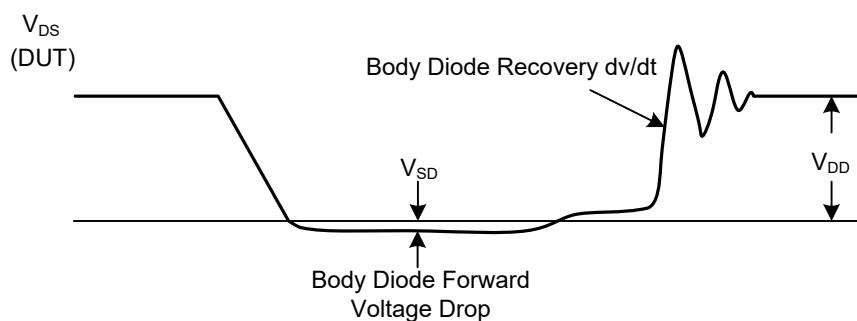
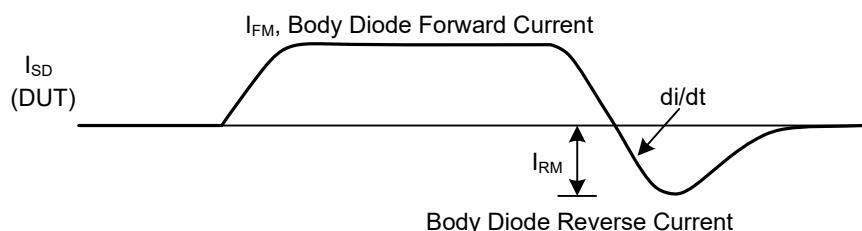
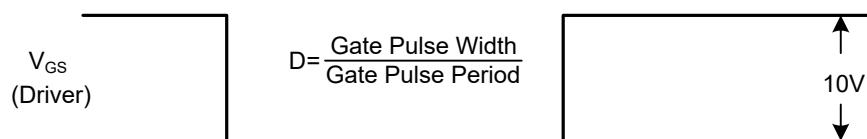
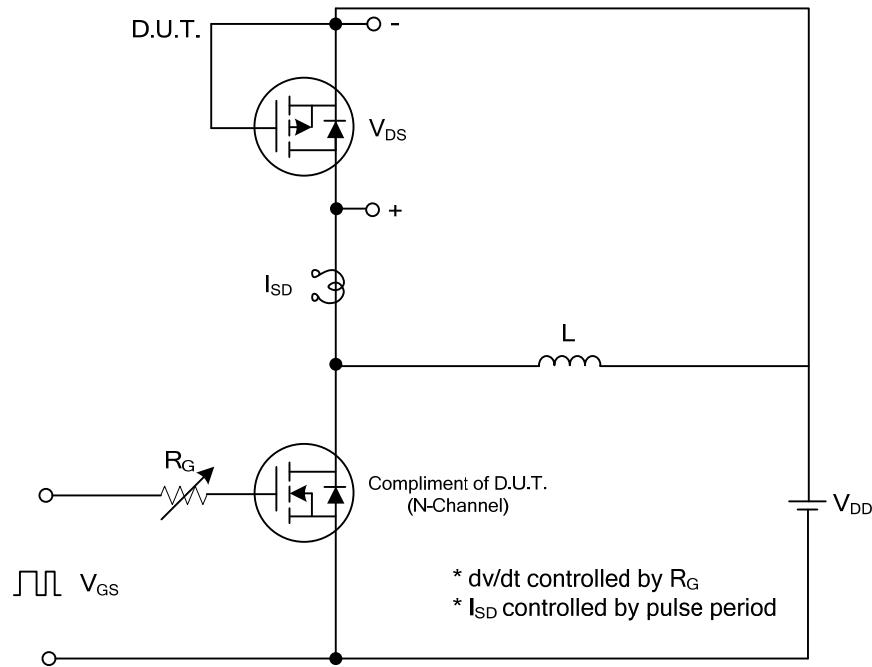
■ ELECTRICAL CHARACTERISTICS ($T_J=25^\circ\text{C}$ unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
STATIC PARAMETERS						
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D=-250\mu\text{A}$, $V_{GS}=0\text{V}$	-150			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-150\text{V}$, $V_{GS}=0\text{V}$			-1	μA
		$V_{DS}=-150\text{V}$, $V_{GS}=0\text{V}$, $T_J=55^\circ\text{C}$			-10	μA
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20\text{V}$, $V_{DS}=0\text{V}$			± 100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(\text{TH})}$	$V_{DS}=V_{GS}$, $I_D=-250\mu\text{A}$	-2.0		-4.0	V
Drain-Source On-State Resistance	$R_{DS(\text{ON})}$	$V_{GS}=-10\text{V}$, $I_D=-1.4\text{A}$			0.75	Ω
		$V_{GS}=-6.0\text{V}$, $I_D=-1.0\text{A}$			0.79	Ω
DYNAMIC PARAMETERS (Note 2)						
Input Capacitance	C_{ISS}	$V_{DS}=-25\text{V}$, $V_{GS}=0\text{V}$, $f=1\text{MHz}$		460		pF
Output Capacitance	C_{OSS}			42		pF
Reverse Transfer Capacitance	C_{RSS}			20		pF
SWITCHING PARAMETERS (Note 1)						
Total Gate Charge	Q_G	$V_{GS}=-10\text{V}$, $V_{DS}=-120\text{V}$, $I_D=-1.4\text{A}$,		18		nC
Gate to Source Charge	Q_{GS}			8		nC
Gate to Drain Charge	Q_{GD}			2.5		nC
Turn-ON Delay Time	$t_{D(\text{ON})}$	$V_{DS}=-75\text{V}$, $V_{GS}=-10\text{V}$, $I_D=-1.4\text{A}$, $R_G=1\Omega$		5		ns
Rise Time	t_R			17		ns
Turn-OFF Delay Time	$t_{D(\text{OFF})}$			16		ns
Fall-Time	t_F			20		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Continuous Source-Drain Diode Current	I_S	$T_C=25^\circ\text{C}$			-1.4	A
Pulse Diode Forward Current	I_{SM}				-5	A
Body Diode Voltage	V_{SD}	$I_S=-1\text{A}$, $V_{GS}=0\text{V}$		-0.8	-1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F=-1.4\text{ A}$, $di/dt=100\text{A}/\mu\text{s}$		32		ns
Body Diode Reverse Recovery Charge	Q_{rr}			112		nC

Notes: 1. Pulse test; pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.

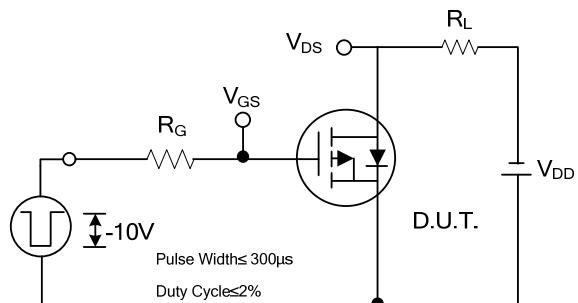
2. Guaranteed by design, not subject to production testing.

■ TEST CIRCUITS AND WAVEFORMS

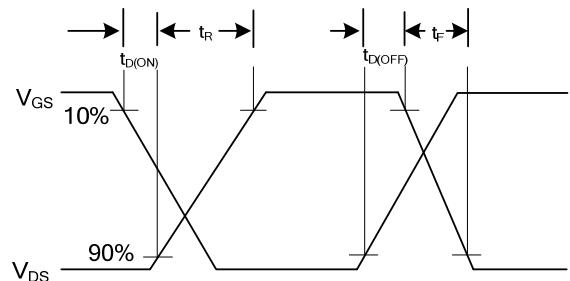


Peak Diode Recovery dv/dt Test Circuit and Waveforms

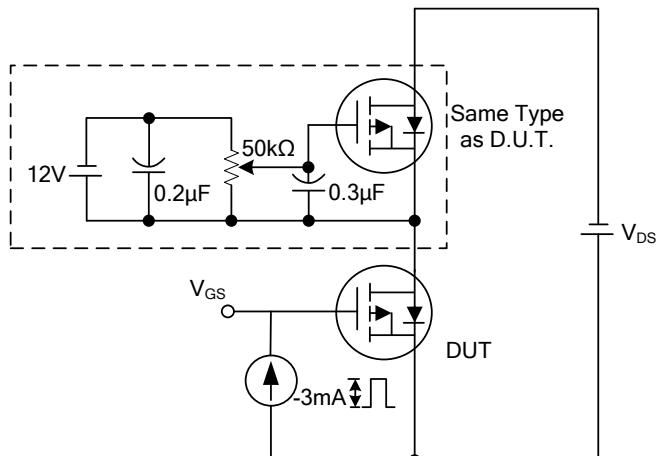
■ TEST CIRCUITS AND WAVEFORMS



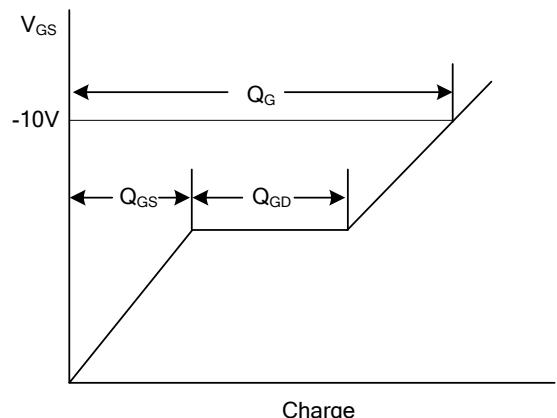
Switching Test Circuit



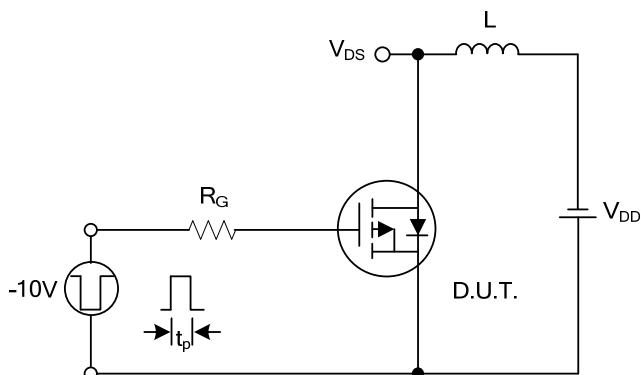
Switching Waveforms



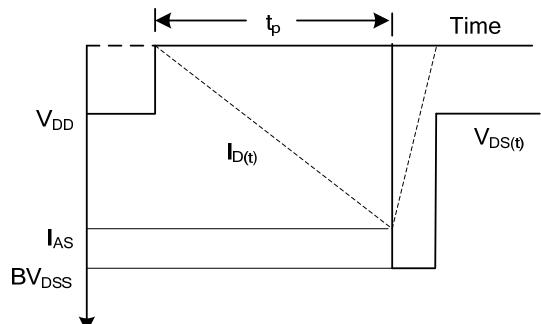
Gate Charge Test Circuit



Gate Charge Waveform

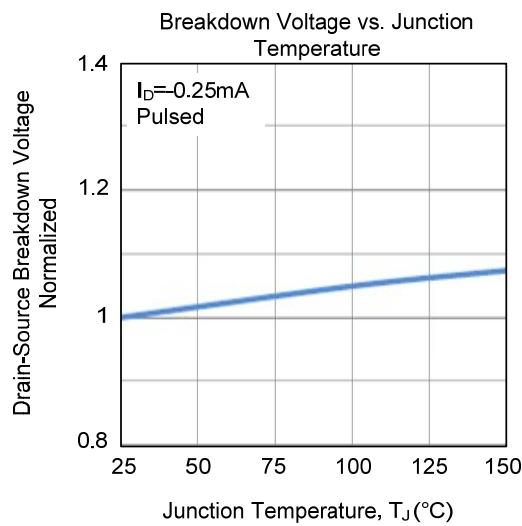
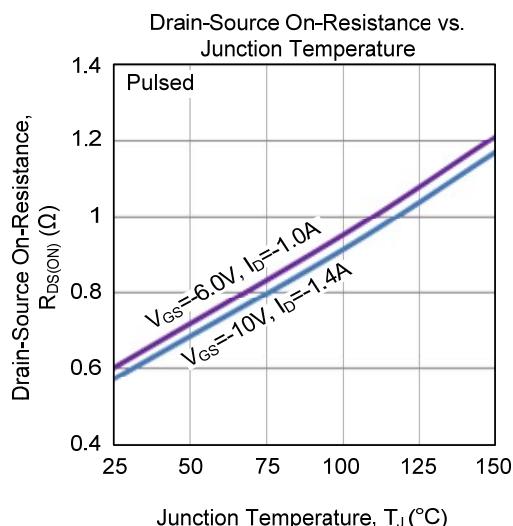
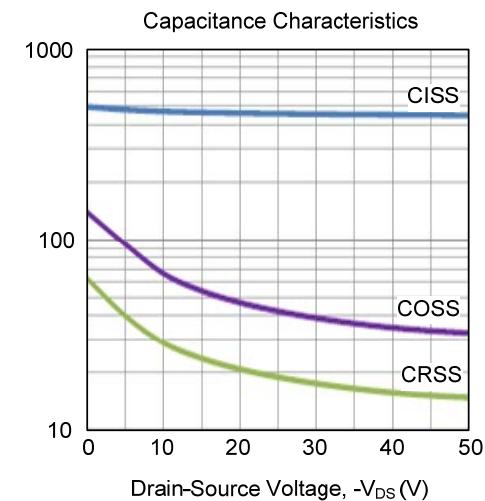
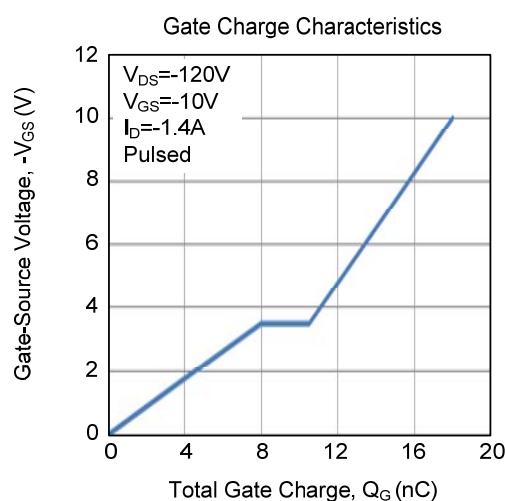
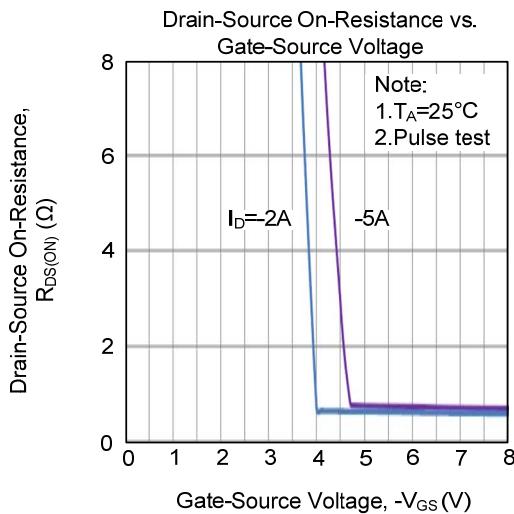
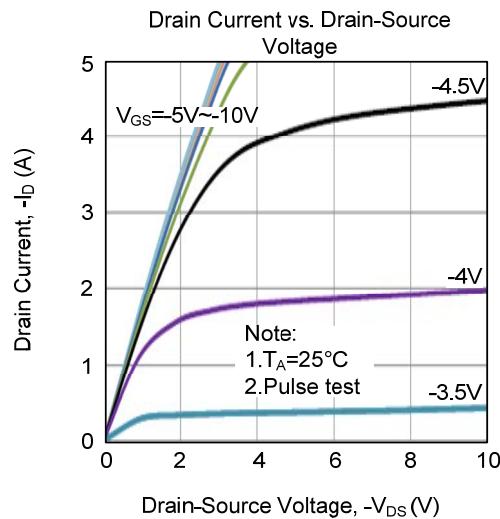


Unclamped Inductive Switching Test Circuit

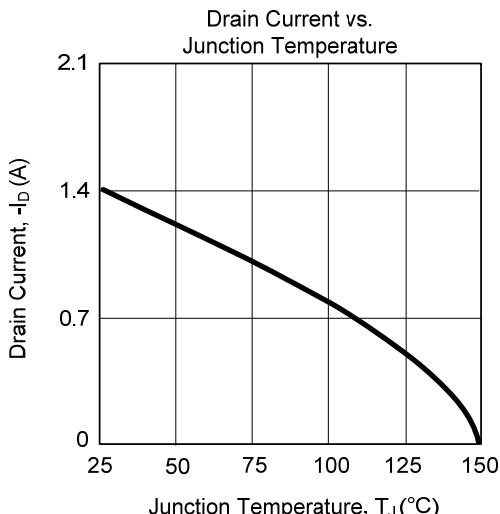
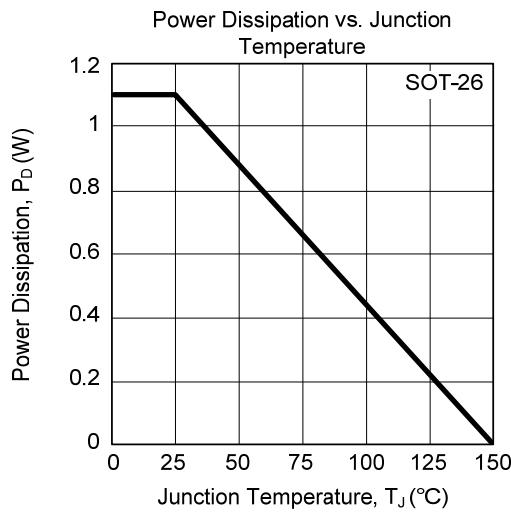
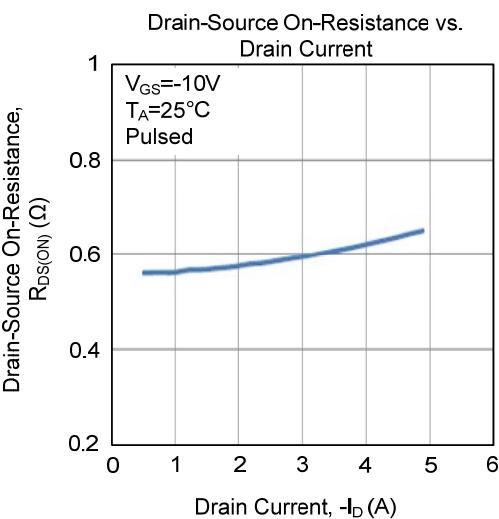
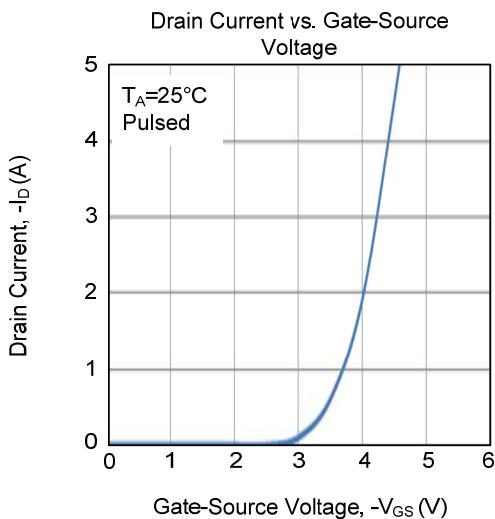
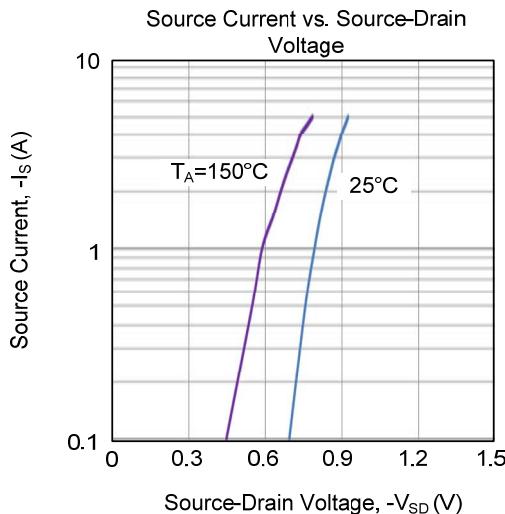
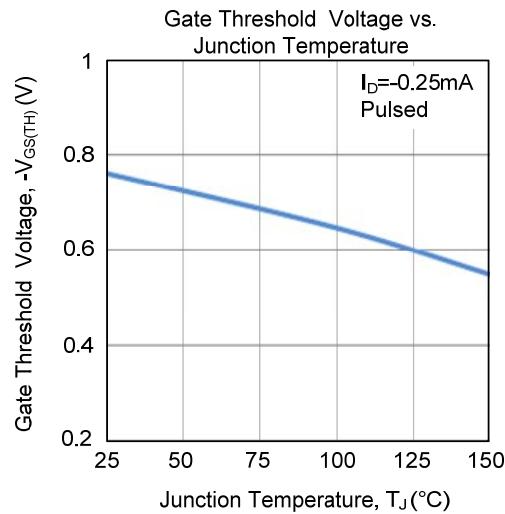


Unclamped Inductive Switching Waveforms

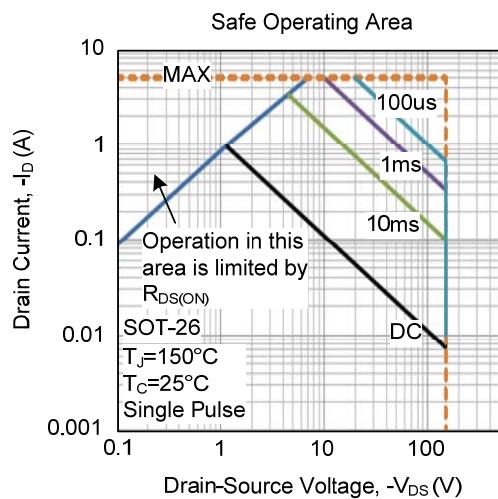
■ TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS (Cont.)



- TYPICAL CHARACTERISTICS (Cont.)



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